

**TO - 92 BIPOLAR TRANSISTORS
TRANSISTOR(NPN)**

FEATURES

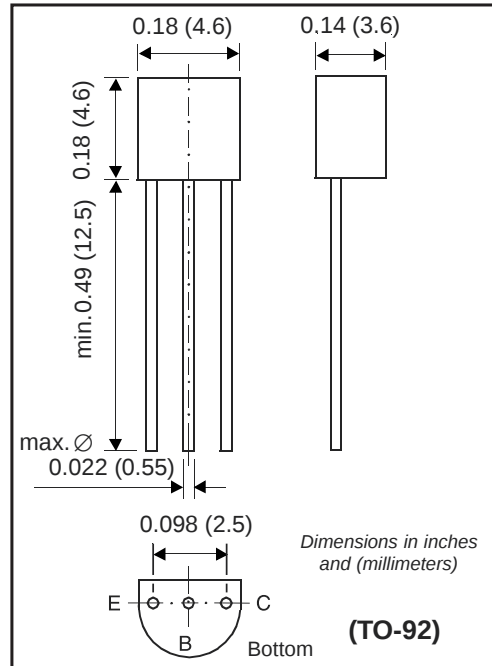
- * Power dissipation
P_{CM}: 625mW(T_{amb}=25°C)
- * Collector current
I_{CM}: 0.6 A
- * Collector-base voltage
V_{(BR)CBO}: 75 V
- * Operating and storage junction temperature range
T_J, T_{stg}: -55°C to +150°C

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-O rate flame retardant
- * Lead: MIL-STD-202E method 208C guaranteed
- * Mounting position: Any
- * Weight: 0.008 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



MAXIMUM RATINGS (@ T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	VALUE	UNITS
Max. Steady State Power Dissipation ⁽¹⁾ @T _A =25°C Derate above 25°C	P _D	625	mW
Max. Operating Temperature Range	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (@ T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Thermal Resistance Junction to Ambient	R _{θJA}	-	-	200	°C/W

Notes : 1. Alumina=0.4*0.3*0.024in.99.5% alumina
2. "Fully ROHS Compliant", "100% Sn plating (Pb-free)".

2011-2

ELECTRICAL CHARACTERISTICS (@TA=25°C unless otherwise noted)

Chataacteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10\text{mA}$, $I_B = 0$)	$V_{(BR)CEO}$	40	-	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	75	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	-	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{Vdc}$, $V_{EB(off)} = 3.0\text{Vdc}$)	I_{CEX}	-	0.01	μA
Collector Cutoff Current ($V_{CB} = 60\text{Vdc}$, $I_E = 0$) ($V_{CB} = 60\text{Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CBO}	-	0.01	μA
		-	10	
Emitter Cutoff Current ($V_{EB} = 3.0\text{Vdc}$, $I_C = 0$)	I_{EBO}	-	0.01	μA
Base Cutoff Current ($V_{CE} = 60\text{Vdc}$, $V_{EB(off)} = 3.0\text{Vdc}$)	I_{BL}	-	20	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $T_A = -55^\circ\text{C}$) ($I_C = 500\text{mA}$, $V_{CE} = 10\text{Vdc}$) (1)	hFE	35	-	-
		40	-	
Collector-Emitter Saturation Voltage (1) ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$) ($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)	$V_{CE(sat)}$	-	0.3	Vdc
		-	1.0	
Base-Emitter Saturation Voltage (1) ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$) ($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)	$V_{BE(sat)}$	0.6	1.2	Vdc
		-	2.0	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product (2) ($I_C = 20\text{mA}$, $V_{CE} = 20\text{Vdc}$, $f = 100\text{MHz}$)	f_T	300	-	MHz
Input Capacitance ($V_{EB} = 0.5\text{Vdc}$, $I_C = 0$, $f = 1.0\text{MHz}$)	C_{ibo}	-	25	pF
Input Impedance ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{ie}	2.0	8.0	kohms
		0.25	1.25	
Voltage Feedback Ratio ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{re}	-	8.0	$\times 10^{-4}$
		-	4.0	
Small-Signal Current Gain ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{fe}	50	300	-
		75	375	
Output Admittance ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$)	h_{oe}	5.0	35	μmhos
		25	200	
Collector Base Time Constant ($I_E = 20\text{mA}$, $V_{CB} = 20\text{Vdc}$, $f = 31.8\text{MHz}$)	$\tau_{b,Cc}$	-	150	ps
Noise Figure ($I_C = 100\mu\text{A}$, $V_{CE} = 10\text{Vdc}$, $R_S = 1.0\text{kohms}$, $f = 1.0\text{kHz}$)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30\text{Vdc}$, $V_{BE(off)} = -0.5\text{Vdc}$, $I_C = 150\text{mA}$, $I_{B1} = 15\text{mA}$)	t_d	-	10	ns
Rise Time		t_r	-	25	
Storage Time	$(V_{CC} = 30\text{Vdc}$, $I_C = 150\text{mA}$, $I_{B1} = I_{B2} = 15\text{mA}$)	t_s	-	225	ns
Fall Time		t_f	-	60	

NOTES : 1. Pulse Test: Pulse Width≤300ms,Duty Cycle≤2.0%
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity

RATING AND CHARACTERISTICS CURVES (PN2222A)

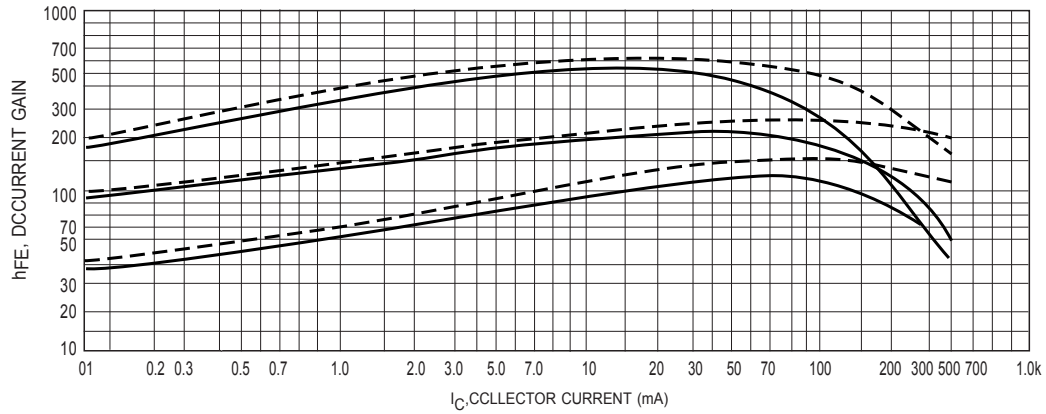


Figure 1. DC Current Gain

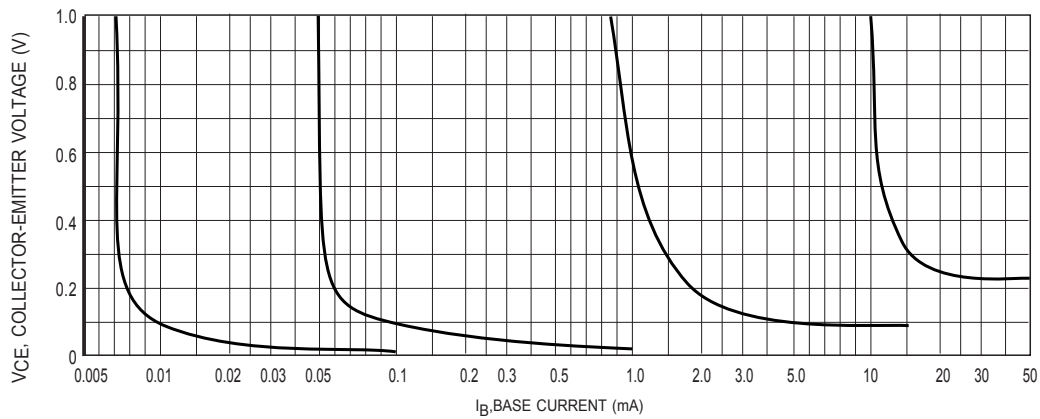


Figure 2. Collector Saturation Region

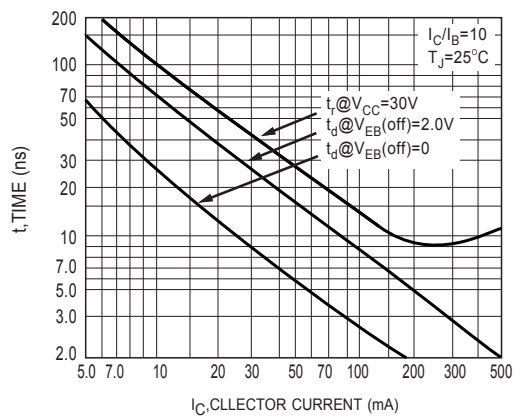


Figure 3. Turn-On Time

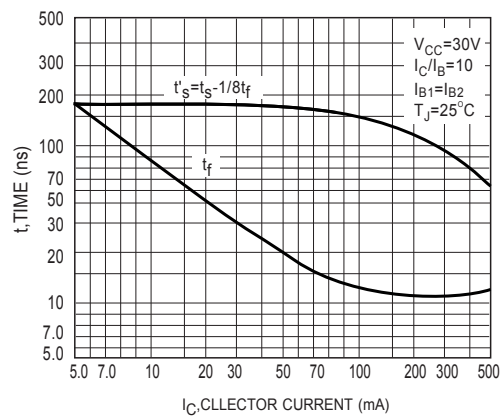


Figure 4. Turn-Off Time

RATING AND CHARACTERISTICS CURVES (PN2222A)

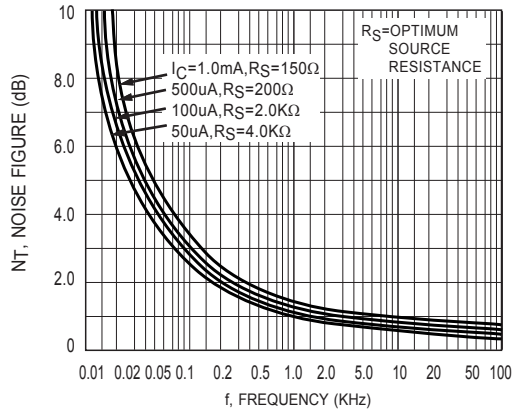


Figure 5.Frequency Effects

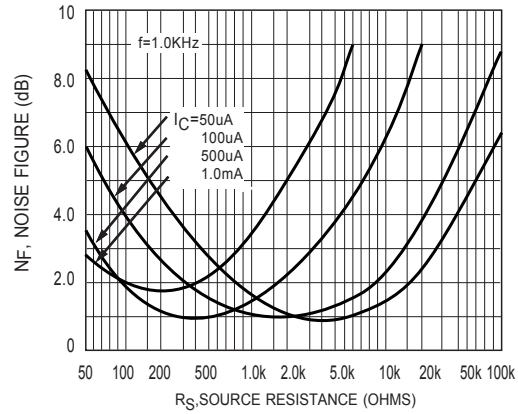


Figure 6.Source Resistance Effects

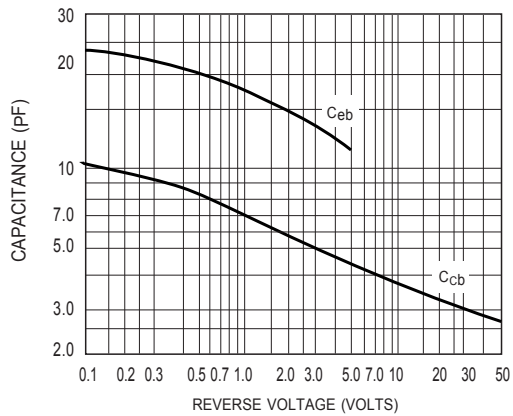


Figure 7.Capacitances

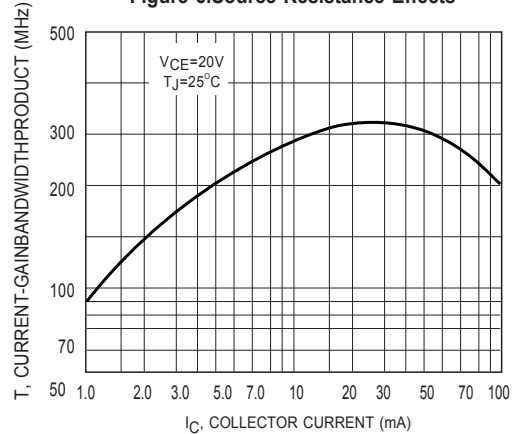


Figure 8.Currunt-Gain Bandwidth Product

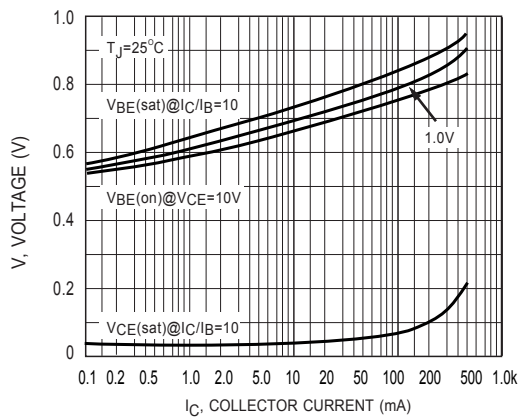


Figure 9."On" Voltages

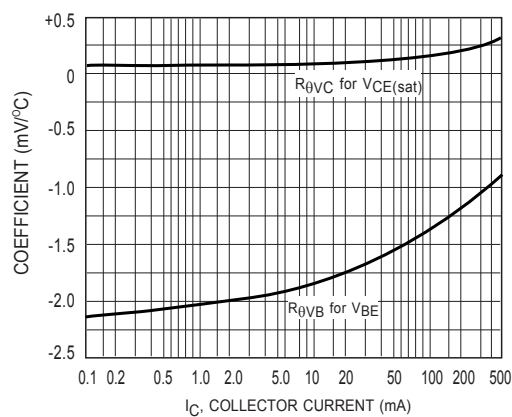


Figure 10.Temperature Coefficients

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